



 **ISOCC 2016**
International SoC Design Conference
13th International SoC Design Conference
October 23-26, 2016 RAMADA PLAZA JEJU HOTEL, Jeju, Korea

Conference Theme

The theme of ISOCC 2016 is **"Smart SoC for Intelligent Things"** Recent IT industries suffer from the huge amount of information. The information requires lots of attention to be used for human, robot, bio, and automotive industry. By providing efficient technology, the information becomes reliable and trust worthy. We try to propose technology for the industries and find the way to give them more reliable and profitable information. The SoC solutions for interface and interaction require new approaches to march into the next level. ISOCC 2016 is looking for novel SoC solutions to provide ways to cooperate with automotive, bio, robot, and IT industries.

News & Notice

- Tentative technical program can be downloaded. [2016-10-02]
- ISOCC 2016 Program Announced ! [2016-09-20]
- Camera-ready submission and Registration page are available. [2016-08-29]
- The decision letters have been sent. (August 29, 2016) [2016-08-29]
- EXTENDED Full Paper Submission Deadline : **August 12, 2016** [2016-07-29]
- Chip Design Contest page is available. [2016-07-15]
- Tutorials Announced! [2016-07-15]
- Keynote speakers Announced! (July 11, 2016) [2016-07-12]

Sunday ~ Wednesday, October 23~26, 2016

Time		Oct. 23 Sunday		
From	Till	2nd Floor		
		Lobby	Ballroom2	Ballroom3
12:30	13:00			
13:00	14:30	REGISTRATION	Tutorial 1-1	Tutorial 2-1
14:30	14:45		Break	
14:45	16:15		Tutorial 1-2	Tutorial 2-2
16:15	16:30		Break	
16:30	18:00		Tutorial 1-3	Tutorial 2-3
18:00	18:30		Break	
18:30	20:30		Welcome Reception	

Time		Oct. 24 Monday								
From	Till	2nd Floor							8th Floor	
		Lobby	Ballroom1	Ballroom2	Ballroom3	Chuja	Mara	Udc	Tanna	
8:00	8:15					CDC 1	CDC 2	CDC 3		
8:15	8:30									
8:30	8:45									
8:45	9:00									
9:00	9:15									
9:15	10:00	REGISTRATION	Opening Ceremony							
10:00	10:45		Keynote 1-1							
10:45	11:00		Keynote 1-2							
11:00	11:45		Break							
11:45	12:30		Keynote 1-3							
12:30	13:45		Keynote 1-4							
			Lunch							
13:45	14:00		Lobby	Ballroom1	Ballroom2	Ballroom3	Ballroom4	Mara	CDC	Tanna
14:00	14:15				213	173	052	050	195	
14:15	14:30				169	228	019	116	208	
14:30	14:45		PEC	CASE1	029	SS1	053	122	222	
14:45	15:00			110	030	059	SS2	133	289	
15:00	15:15			124	032			210	288	
15:15	15:30						257			
15:30	15:45		Chip Design Contest (CDC) Poster Exhibition							
15:45	16:00								Intelligent IC Workshop 13:00 ~ 17:30	
16:00	16:15			007	260	127	258	201		
16:15	16:30			033	094		259	207		
16:30	16:45		ARM1	152	182	074	274	236		
16:45	17:00			193	DIGITAL1	DIGITAL2	SS2	280		253
17:00	17:15			232			281	282		
17:15	17:30			291		027		283		
17:30	18:30	Banquet								
18:30	19:00									
19:00	19:30									
19:30	20:30									

[CDC-P103] An 11-bit 50-MS/s Pipeline ADC Using Circuit-Sharing Techniques

Seungheun Song, Chulkyu Park, Hyunki Jeong, Sanghyung Kim, and Joongho Choi
University of Seoul, Korea

[CDC-P104] SIMD Based Multi-Core System-on-Chip Design for Real-Time Signal Processing

Junsang Seo, Inkyu Jeoung, Jaeyoung Kim and Jong-Myon Kim
University of Ulsan, Korea

[CDC-P105] Offset-Canceling Current-Sampling Sense Amplifier for Resistive Nonvolatile Memory in 65-nm CMOS

Taehui Na, Byungkyu Song, and Seong-Ook Jung
Yonsei University, Korea

[CDC-P106] An Implementation of MIMO PHY Modulator for IEEE 802.11n WLAN System

Minjoon Kim, and Jaeseok Kim
Yonsei University, Korea

[CDC-P107] Multi-Rate Clock and Data Recovery Circuit For Display Interface

Ki-Hyun Pyun, Dae-Hyun Kwon, and Woo-Young Choi
Yonsei University, Korea

[CDC-P108] A Single Inductor Multiple Output(SIMO) Buck/Boost DC-DC Converter with Output Error-Driven Random Control

Hyunbin Park, Minseob Sim and Shiho Kim
Yonsei University, Korea

[CDC-P109] Comparison Between Silicon Data and Simulated Data at Near-threshold Region in 65-nm CMOS

Juhyun Park, Hanwool Jeong, Hyun Jun Kim, and Seong-Ook Jeong
Yonsei University, Korea

[CDC-P110] Design of Ka-band Low-noise Amplifier

Mingyo Park, Gyoungjune Jeon and Byung-Wook Min
Yonsei University, Korea

[CDC-P111] Design of Ka-band Power Amplifier

Mingyo Park, Bosung Suh and Byung-Wook Min
Yonsei University, Korea

Multi-Rate Clock and Data Recovery Circuits For Display Interfaces

Ki-Hyun Pyun, Dae-Hyun Kwon, and Woo-Young Choi

Department of Electrical and Electronic Engineering, Yonsei University, Seoul 120-749, Korea

I. INTRODUCTION

In display applications, the amount of video data rapidly increases due to demands for higher resolution and frame rates, and clock and data recovery (CDR) circuits that can cover multiple data rates are very desirable. Conventional multi-rate CDR circuits consist of the multiple VCOs [1],[2]. However, it is very challenging to design VCOs having the same VCO gain. To solve this problem, a multi-mode phase detector (PD) can be used for multi-rate CDR. We propose a new multi-rate CDR architecture based on a multi-mode rotational bang-bang phase detector (MRBPD), which can operate at 3.5-Gb/s, 7.0-Gb/s and 14-Gb/s.

II. DESCRIPTION

Fig. 1 shows structure of our multi-rate CDR circuit having MRBPD, charge pump, 8-phase VCO, and controller. The controller generates 4-bit signal (T0, T1, T2, T3) depending on FBD0 and FBD1, which represent the data rate. The MRBPD supports full-rate, half-rate and quarter-rate phase detection enabling the multi-mode CDR operation.

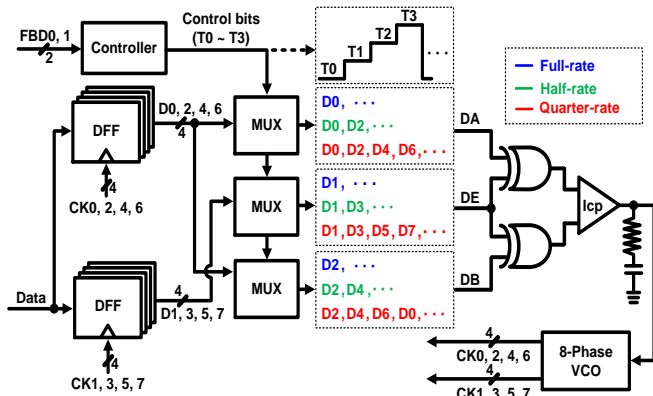


Fig. 1. Proposed multi-rate CDR circuit.

Fig. 2 shows timing diagram for three different data rates. If the data rate is 3.5-Gb/s, the MRBPD operates as a full-rate binary PD. In this case, controller operates in state 1. If the data rate is 7.0-Gb/s, the MRBPD operates as a half-rate binary PD. In this case, controller repeatedly operates in state 1 and state 3 back and forth. If the data rate is 14.0-Gb/s, the MRBPD operates as a quarter-rate binary PD. In this case, controller repeatedly operates in state 1, state 2, state 3 and state 4 rotationally.

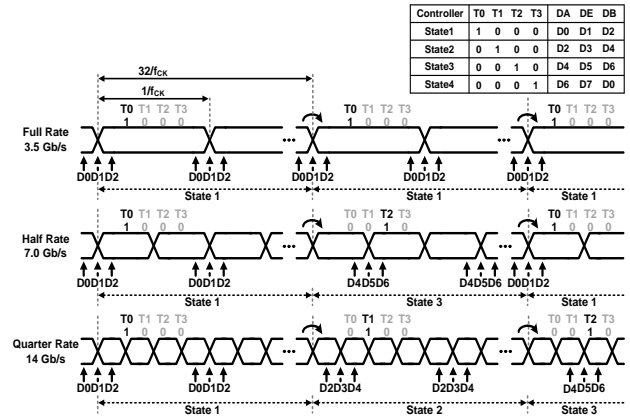


Fig. 2. Timing diagram of multi-rate operation

III. CHIP IMPLEMENTAION AND RESULTS

A die photograph of the CDR is shown in Fig. 2. It is fabricated in 65nm Samsung CMOS process. The CDR occupies 0.017mm². Fig. 3 shows measured eye diagram of the recovered output data with full/ half/ quarter-rate operations respectively.

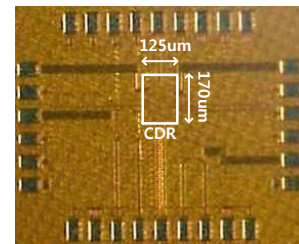


Fig. 3. Photomicrograph of the proposed chip.

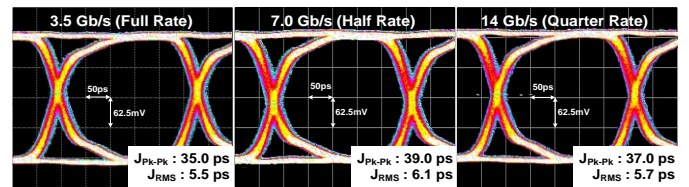


Fig. 4. The eye diagram of recovered data.

REFERENCE

- [1] J. Zhou, et al., "A Dual-Mode VCO based Low-Power Synthesizer with Optimized Automatic Frequency Calibration for Software-Defined Radio," in IEEE ISCAS. Papers, May. 2011, pp. 1145-1148..
- [2] Y. Dong, et al., "A self-calibrating multi-VCO PLL scheme with leakage and capacitive modulation mitigations," in IEEE ISCAS. Papers, May. 2013, pp. 1400-1403.

This work was supported by the National Research Foundation of Korea grant funded by the Korea government (MEST) [2015R1A2A2A01007772]. The authors are also thankful to IDEC for MPW and EDA software support. Details of our multi-mode CDR will be presented APCAS 2016.



Multi-Rate Clock and Data Recovery Circuit For Display Interface

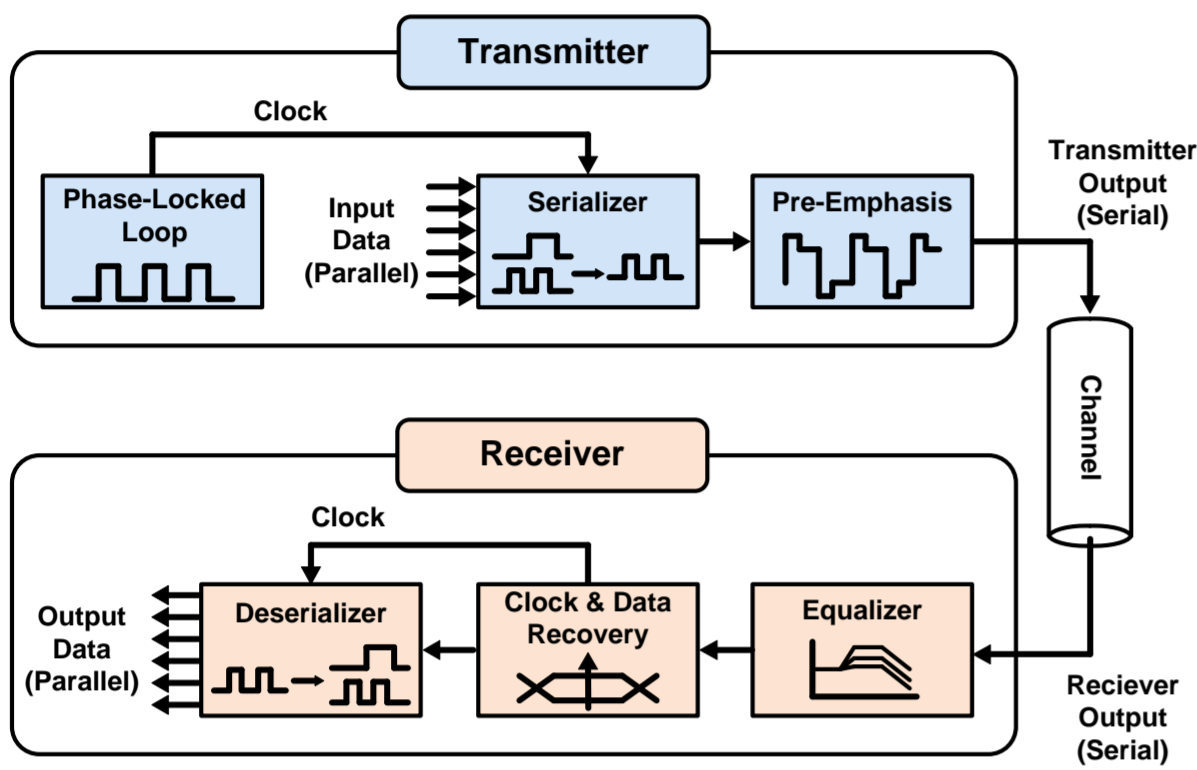
Ki-Hyun Pyun, Dae-Hyun Kwon, and Woo-Young Choi

Department of Electrical and Electronic Engineering, Yonsei University, Seoul, Korea

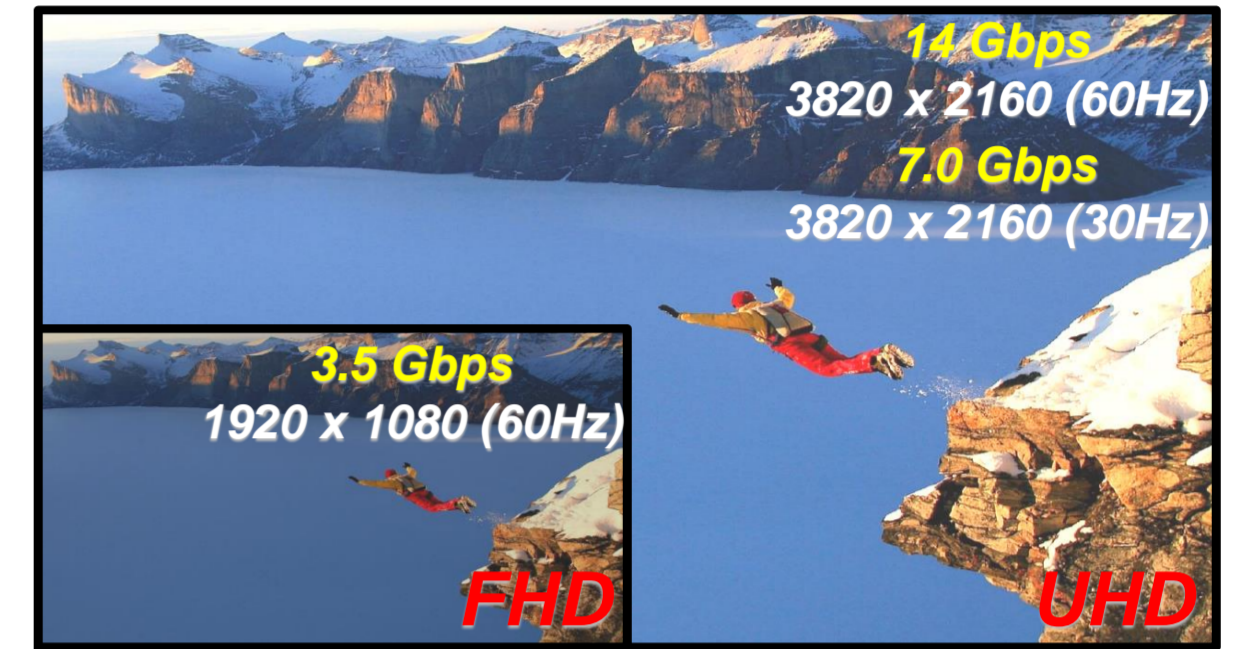
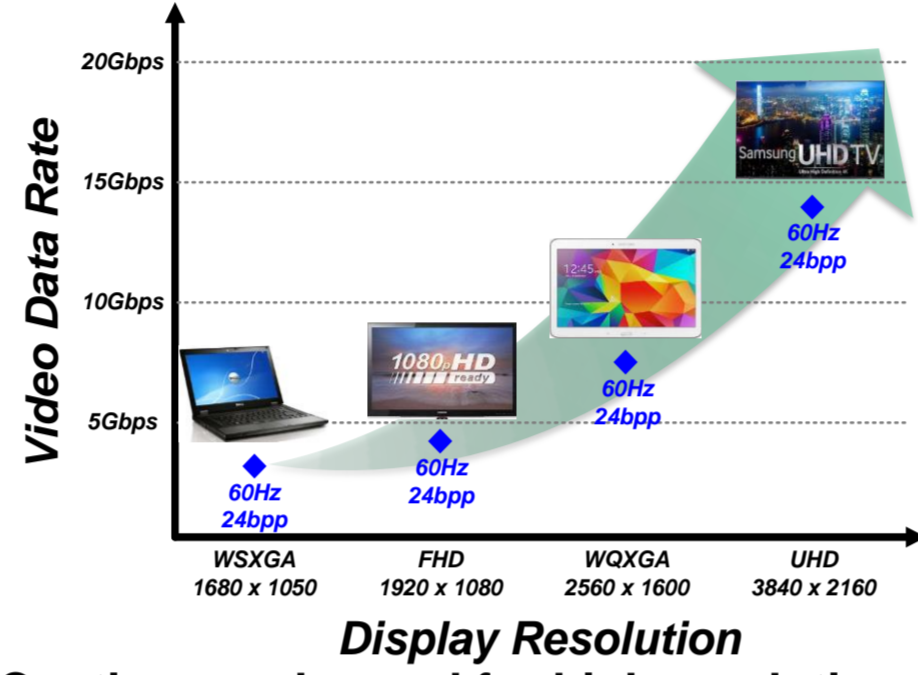
Receiver for Display Interface Applications

High-Speed Serial Link Display Interface

[Block Diagram of Serial Link]



[Display Interface Trends]

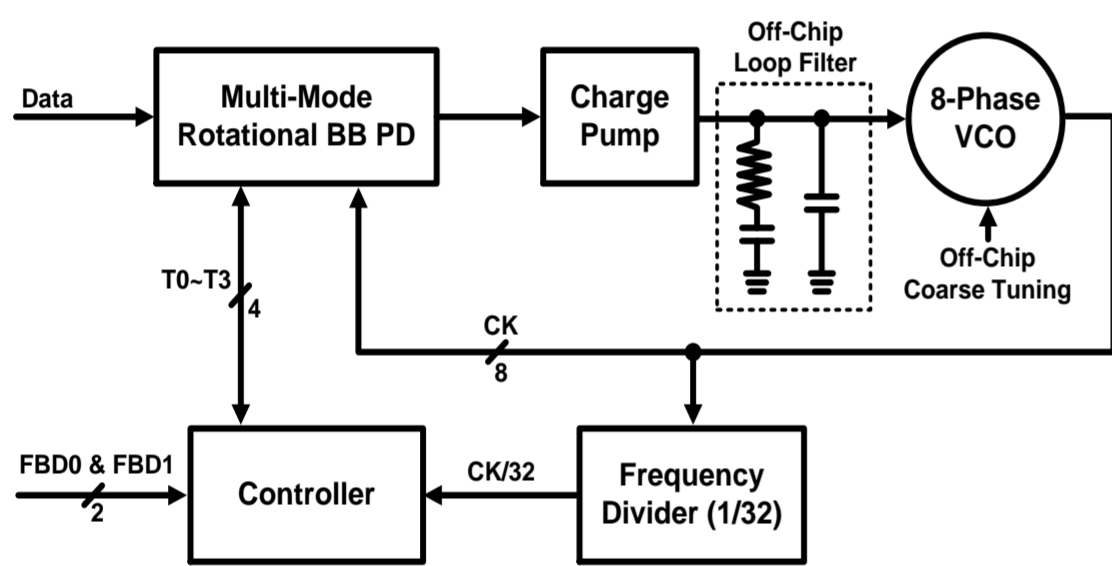


- Continuous demand for high resolution and frame rate
- Support the maximum data rate over 10Gb/s

- Support FHD 60Hz and UHD 30/60Hz
- Need multi-rate CDR

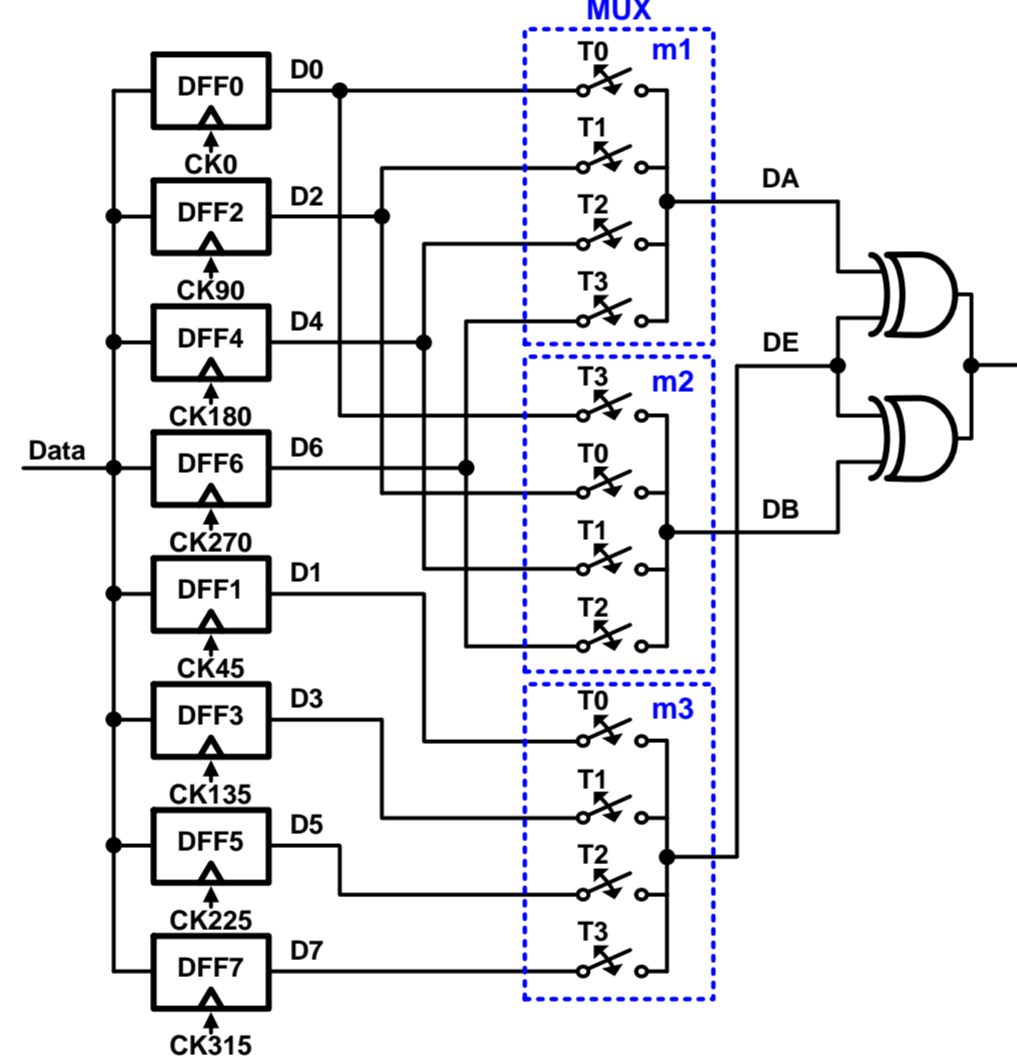
Multi-Rate CDR Design

[Multi-Rate CDR Circuit]

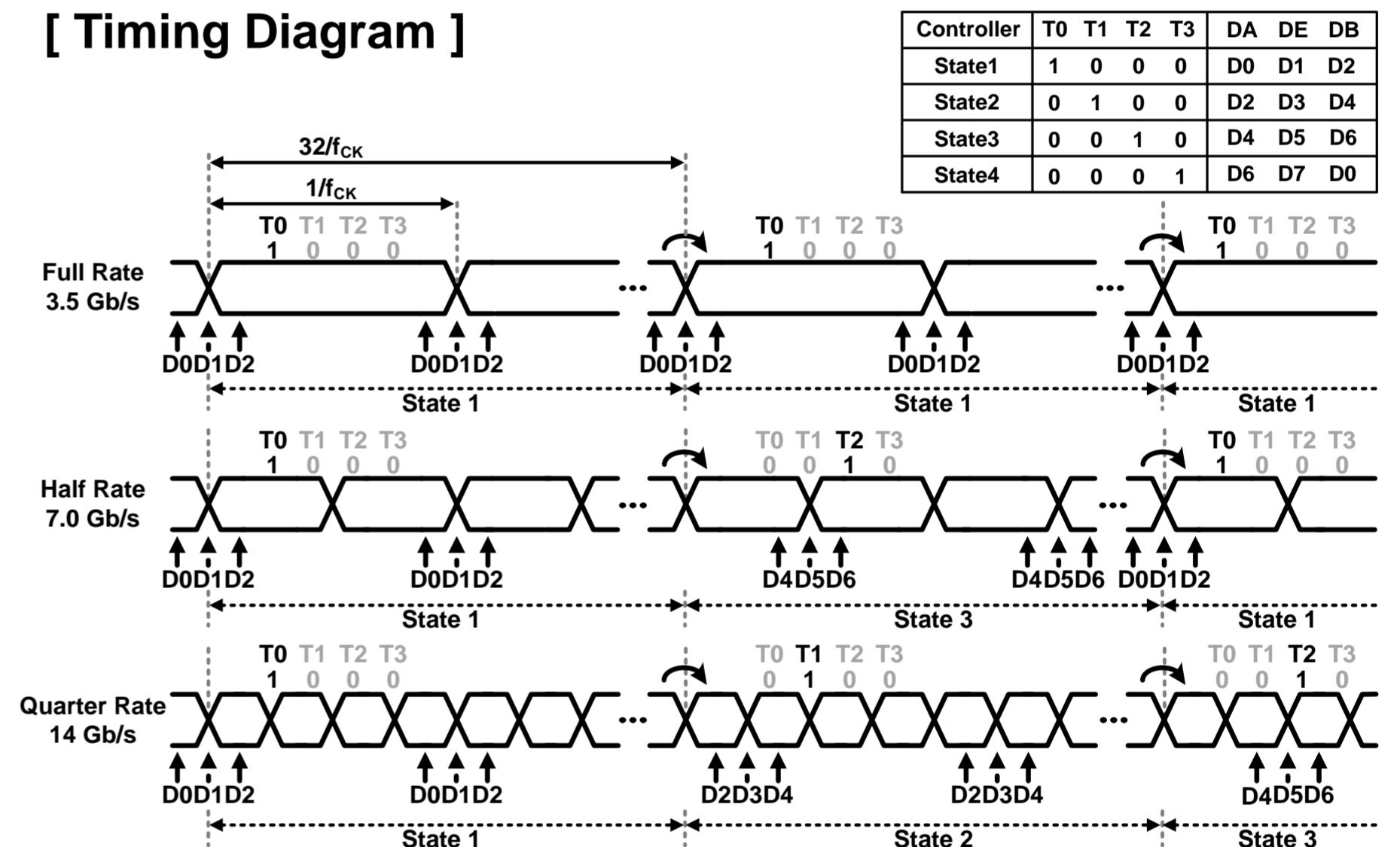


- Multi-Mode Rotational Bang-Bang PD (MRBPD)
- Controller
- Frequency Divider
- 8-Phase VCO
- Charge Pump

[MRBPD Circuit]

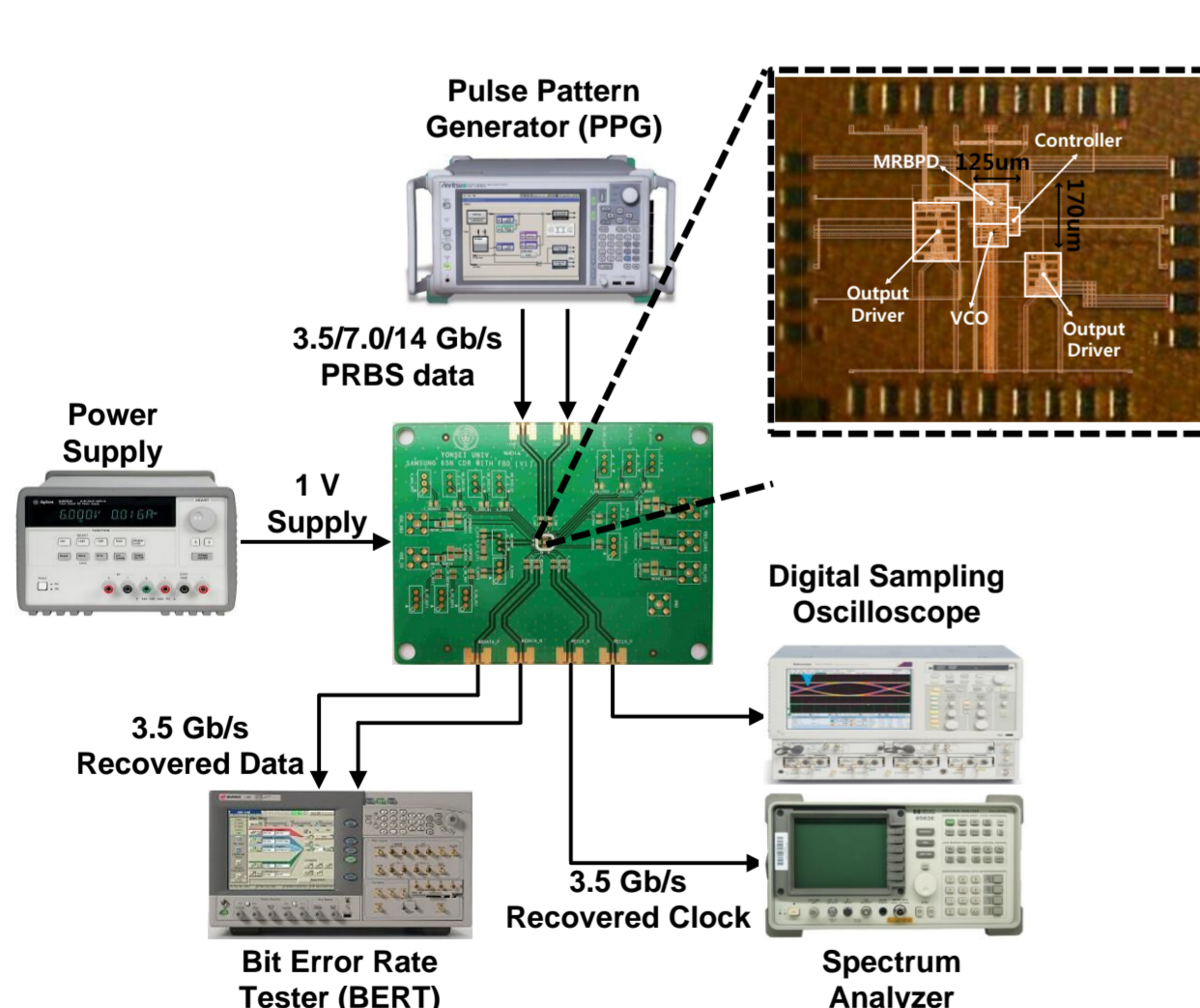


[Timing Diagram]



Measurement Results

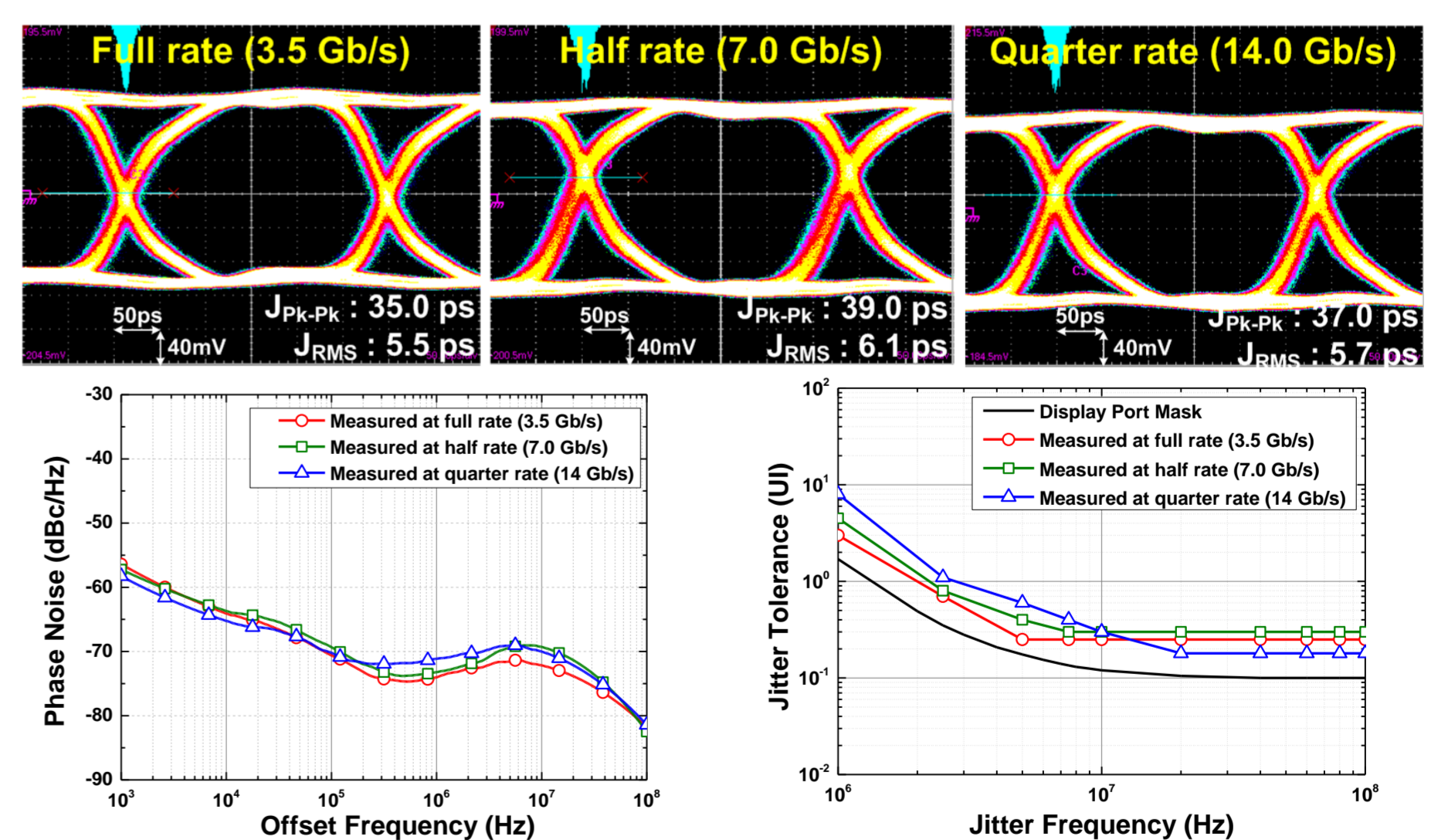
[Experimental Setup]



[Summary]

Data-rate	3.5 / 7.0 / 14.0 Gb/s
Technology	CMOS 65-nm process
Supply Voltage	1.0 V
Core Area	0.025 mm ²
Power consumption	9mW @ 14.0 Gb/s
RMS Jitter	5.7 ps @ 14.0 Gb/s
Power Efficiency	0.64 pJ/bit

[EYE Diagram & Phase Noise & Jitter Tolerance]



Conclusion

- Multi-rate CDR with multi-mode rotational BBPD is realized in 65-nm CMOS Technology.
- A multi-mode rotational BBPD can support full-, half-, and quarter-rate phase detection.
- 3.5-/ 7.0-/14.0-Gb/s data are successfully received with error-free condition.